



# 350mA Small Single Surface Mounted Schottky Diode

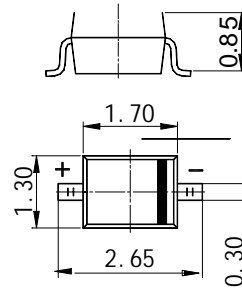
## Description

## Mechanical Dimensions

SD103CWS



SOD-323



Unit: mm

## FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance

MARKING: SD103AWS: S4  
SD103BWS: S5  
SD103CWS: S6

Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$ 

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak reverse voltage	$V_{RRM}$				
Working Peak DC Blocking Voltage	$V_{RWM}$	40	30	20	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	$I_{FM}$	350			mA
Repetitive Peak Forward Current @ $t \leq 1.0s$	$I_{FRM}$	1.5			A
Power Dissipation	$P_d$	200			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	300			$^\circ\text{C}/\text{W}$
Storage temperature	$T_{STG}$	-65~+125			$^\circ\text{C}$

Electrical Ratings @ $T_A=25^\circ\text{C}$ 

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40			V	$I_R=10\mu\text{A}$
SD103AWS		30				$I_R=10\mu\text{A}$
SD103BWS		20				$I_R=10\mu\text{A}$
Forward voltage	$V_F$			0.37 0.60	V	$I_F=20\text{mA}$ $I_F=200\text{mA}$
Reverse current	$I_{RM}$			5.0		$\mu\text{A}$
SD103AWS						
SD103BWS						
Capacitance between terminals	$C_T$		50		pF	$V_R=0\text{V}, f=1.0\text{MHz}$
Reverse Recovery Time	$t_{rr}$		10		ns	$I_F=I_R=200\text{mA}$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$



## Typical Characteristics

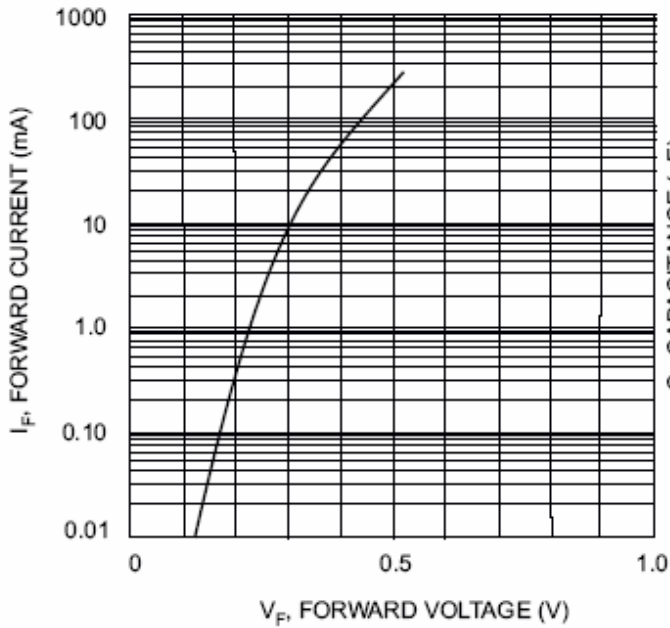


Fig. 1 Typical Forward Characteristics

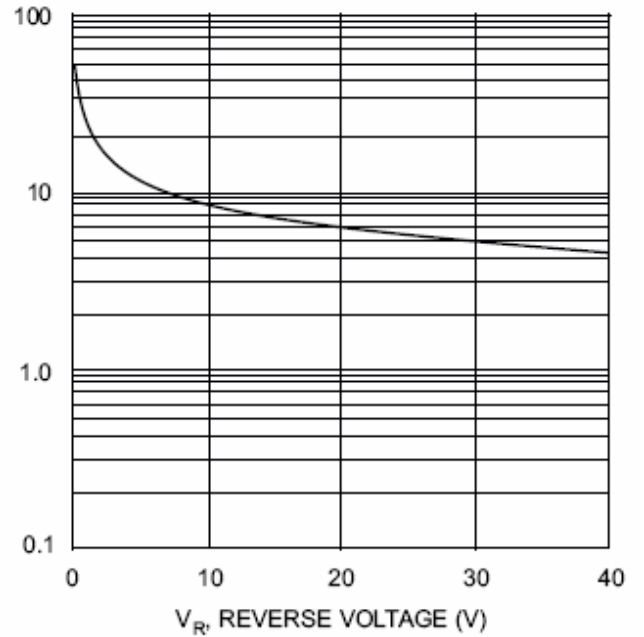


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage